

# The Ni-Pd-Si (Nickel-Palladium-Silicon) System

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## Introduction

Only one isothermal section for the Ni-Pd-Si system has been established and is reported here.

## Binary Systems

The Ni-Pd system [Massalski2] (Fig. 1) is an isomorphous system with a minimum of 1237 °C at ~45 at.% Pd.

The Ni-Si system [Massalski2] (Fig. 2) has eight intermediate phases—Ni<sub>3</sub>Si (β<sub>1</sub>), Ni<sub>3</sub>Si (β<sub>2</sub> and β<sub>3</sub>), Ni<sub>31</sub>Si<sub>12</sub> (γ'), Ni<sub>2</sub>Si (δ), Ni<sub>2</sub>Si (θ), Ni<sub>3</sub>Si<sub>2</sub> (ε and ε'), NiSi (ξ), and NiSi<sub>2</sub> (α and β)—of which several phases, Ni<sub>3</sub>Si (β<sub>2</sub> and β<sub>3</sub>), Ni<sub>3</sub>Si<sub>2</sub> (ε and ε'), and NiSi<sub>2</sub> (α and β) exist in polymorphic forms with polymorphic transition temperatures of ~1165, 830, and 981 °C, respectively. The γ', θ, and ξ phases melt congruently at 1242, 1306, and 992 °C, respectively. The β<sub>1</sub>, β<sub>3</sub>, δ, ε', and ζ phases form through peritectic or peritectoid reactions: L + γ' ↔ β<sub>3</sub> at 1178 °C, L + θ ↔ δ at 1255 °C, L + (Si) ↔ ζ' at 993 °C, γ + β<sub>2</sub> ↔ β<sub>1</sub> at 1035 °C, and θ + ξ ↔ ε at 845 °C. γ is the fcc terminal solid solution (Ni). There are nine eutectic or eutectoid reactions in the Ni-Si system: L ↔ γ + β<sub>3</sub> at 1145 °C, L ↔ γ' + δ at 1215 °C, L ↔ θ + ξ at 964 °C, L ↔ ζ + ξ at 966 °C, β<sub>2</sub> ↔ β<sub>1</sub> + γ' at 990 °C, θ ↔ δ + ε at 825 °C, ε' ↔ δ + ε at

820 °C, ε ↔ ε' + ξ at 800 °C, and ε ↔ ε' + δ at 820 °C. The γ', δ, ξ, and ζ phases are single composition phases.

The Pd-Si system [Massalski2] (Fig. 3) has five intermediate phases—PdSi (ξ), Pd<sub>2</sub>Si (ρ), Pd<sub>3</sub>Si (π), Pd<sub>9</sub>Si<sub>2</sub> (κ), and Pd<sub>5</sub>Si (η). The ρ, π, and η phases melt congruently at 1394, 1070, and 835 °C, respectively. A polymorphic form of Pd<sub>2</sub>Si phase, Pd<sub>2</sub>Si' (ρ'), forms through a peritectic reaction ρ + L ↔ ρ' at 1090 °C. The PdSi (ξ) and Pd<sub>9</sub>Si<sub>2</sub> (κ) phases form through peritectic reactions L + ρ ↔ ξ at 900 °C and L + ξ ↔ κ at 823 °C. The ξ, κ, and η phases exist only at the high temperatures and undergo eutectoid transformations: ξ ↔ ρ' + (Si) at 824 °C, κ ↔ η + π at 772 °C, and η ↔ π + (Pd) at 727 °C. There are four eutectic reactions: L ↔ (Pd) + η at 821 °C, L ↔ η + κ at ≈820 °C, L ↔ π + ρ at 1050 °C, and L ↔ ξ + (Si) at 892 °C.

## Binary and Ternary Phases

The three binary systems Ni-Pd, Pd-Si, and Ni-Si have 11 intermediate phases with several phases of the Ni-Si system having polymorphic forms. In the Ni-Pd-Si system, existence of two ternary intermediate phases, Ni<sub>18</sub>Pd<sub>7</sub>Si<sub>9</sub> and NiPd<sub>2</sub>Si, have been reported. The binary and ternary phases of the Ni-Pd-Si system and their structure data are given in Table 1.

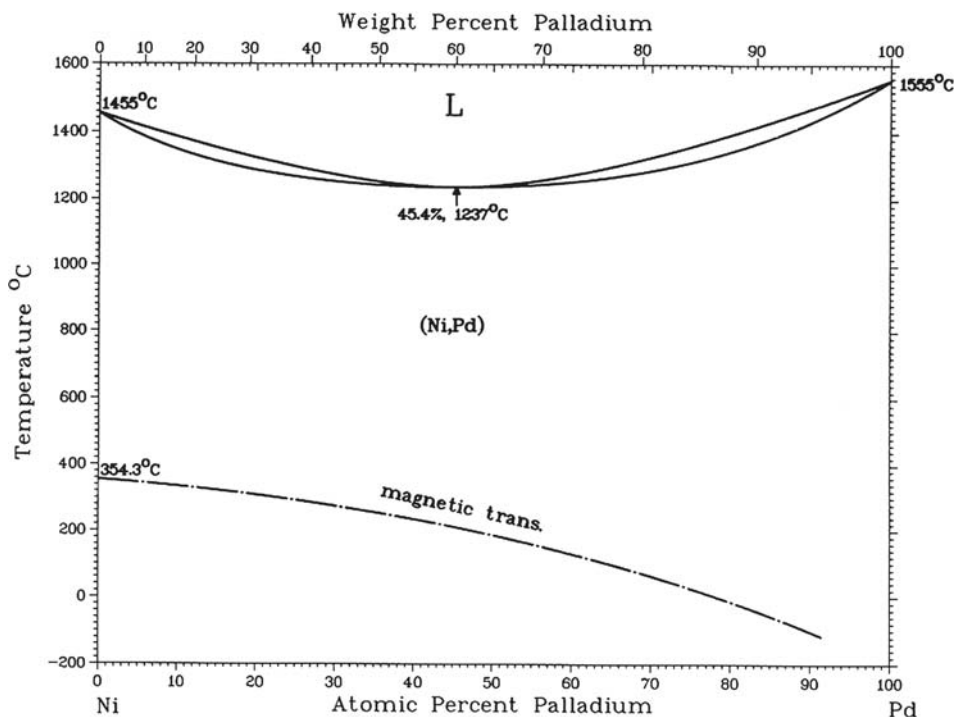


Fig. 1 Ni-Pd binary phase diagram [Massalski2]

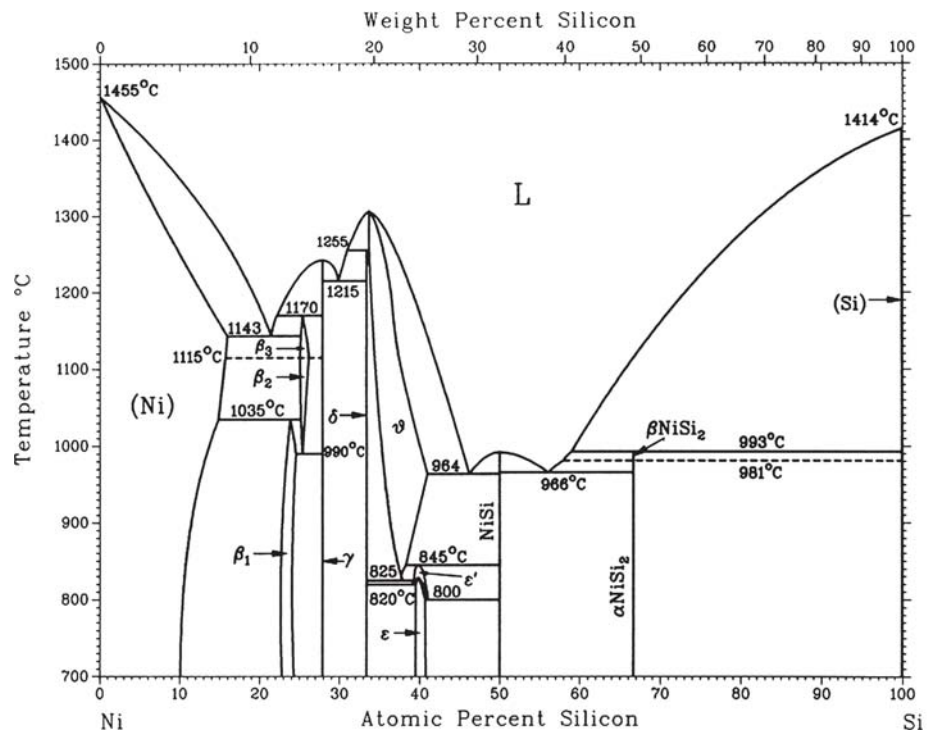


Fig. 2 Ni-Si binary phase diagram [Massalski2]

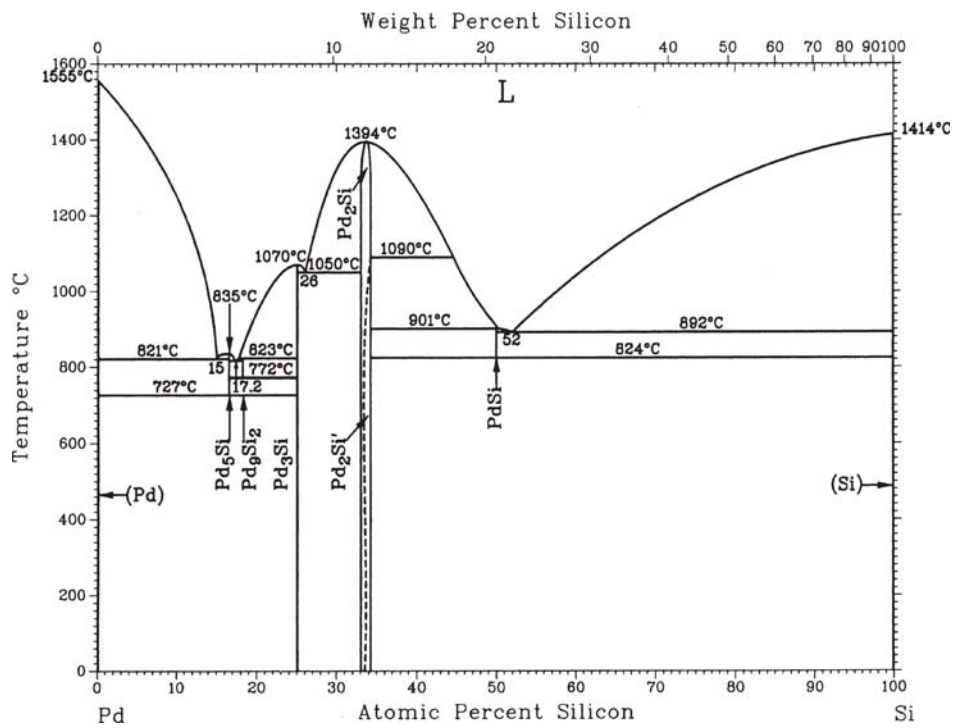


Fig. 3 Pd-Si binary phase diagram [Massalski2]

## Section II: Phase Diagram Evaluations

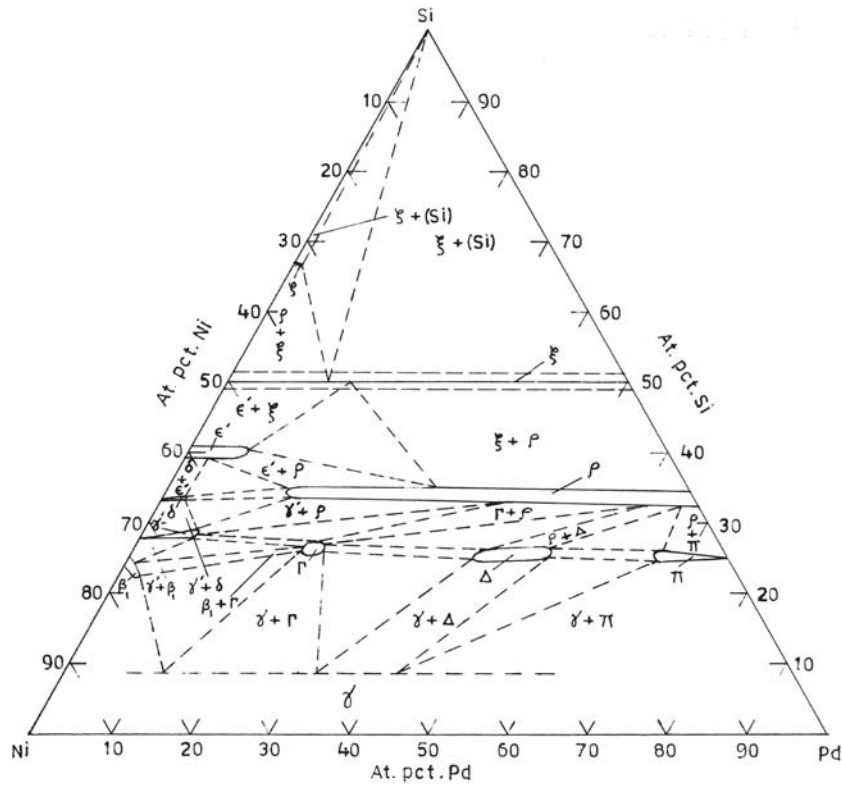


Fig. 4 800 °C isothermal section of Ni-Pd-Si system

Table 1 Phases of the Ni-Pd-Si system and their structure data

Phase designation	Composition, at. %	Pearson's symbol	Space group	Type	Lattice parameter, nm		
					<i>a</i>	<i>b</i>	<i>c</i>
γ	(Ni), (Pd)	<i>cF4</i>	<i>Fm<math>\bar{3}m</math></i>	Cu	...	...	...
(Si)	(Si)	<i>cF8</i>	<i>Fd<math>\bar{3}m</math></i>	C (Diamond)	...	...	...
β <sub>1</sub>	Ni <sub>3</sub> Si (22.8-24.5)	<i>cP4</i>	<i>Pm<math>\bar{3}m</math></i>	AuCu <sub>3</sub>	0.350	...	...
β <sub>2</sub>	Ni <sub>3</sub> Si (24.5-25.5)	<i>mC16</i>	...	GePt <sub>3</sub>	0.697	0.625	0.507
β <sub>3</sub>	Ni <sub>3</sub> Si (24.5-25.5)	<i>mC16</i>	...	...	0.704	0.626	0.508
γ'	Ni <sub>31</sub> Si <sub>12</sub>	<i>hP43</i>	<i>P321</i>	Ni <sub>31</sub> Si <sub>12</sub>	0.667	...	1.228
δ	Ni <sub>2</sub> Si (33.3)	<i>oP12</i>	<i>Pnma</i>	Co <sub>2</sub> Si	0.706	0.499	0.372
ε	Ni <sub>2</sub> Si (33.4-41.0)	<i>hP6</i>	<i>P6<sub>3</sub>/m</i>	Ni <sub>2</sub> Si	0.3805	...	0.489
ε	Ni <sub>3</sub> Si <sub>2</sub>	<i>oP8</i>	...	...	...	...	...
ε'	Ni <sub>3</sub> Si <sub>2</sub>	...	...	...	...	...	...
ξ	NiSi	<i>oP8</i>	<i>Pnma</i>	MnP	0.562	0.518	0.334
ζ	NiSi <sub>2</sub>	<i>cF12</i>	<i>Fm<math>\bar{3}m</math></i>	CaF <sub>2</sub>	0.5406	...	...
ζ'	NiSi <sub>2</sub>	...	...	...	...	...	...
η	Pd <sub>5</sub> Si	...	...	...	...	...	...
κ	Pd <sub>4</sub> Si <sub>2</sub>	...	...	...	...	...	...
π	Pd <sub>3</sub> Si	<i>oP16</i>	<i>Pnma</i>	<i>cFe<sub>3</sub></i>	0.5735	0.7555	0.5260
ρ	Pd <sub>2</sub> Si	<i>hP9</i>	<i>P6<math>\bar{2}m</math></i>	Fe <sub>2</sub> P	0.6496	...	0.3433
ρ'	Pd <sub>2</sub> Si'	...	...	...	...	...	...
ξ	PdSi	<i>oP8</i>	<i>Pnma</i>	MnP	0.56173	0.33909	0.61534
Δ	NiPd <sub>2</sub> Si	...	...	...	...	...	...
Γ	Ni <sub>18</sub> Pd <sub>7</sub> Si <sub>9</sub>	...	...	Pd <sub>25</sub> Ge	0.6835	...	0.9916

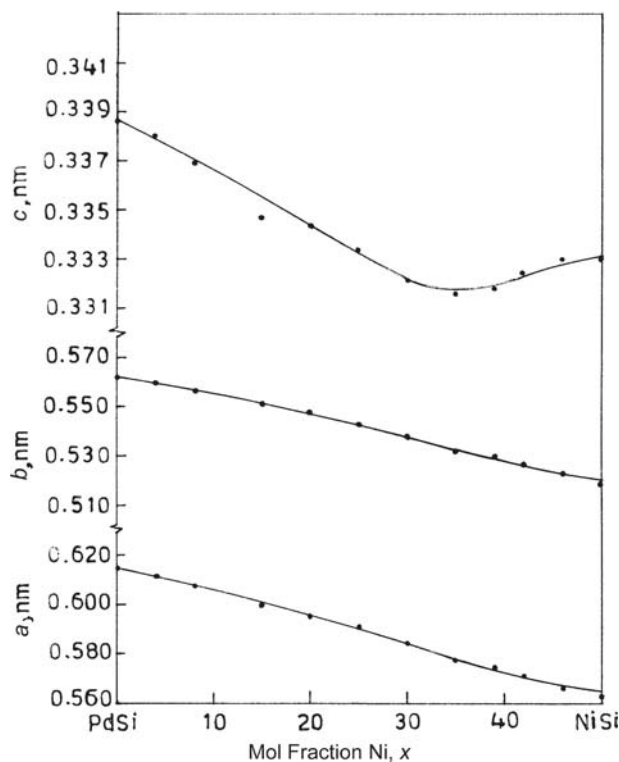


Fig. 5 Lattice parameter of  $\text{Pd}_{50-x}\text{Ni}_x\text{Si}_{50}$  alloys (annealed at  $900^\circ\text{C}$ ) as a function of Ni content  $x$

## Ternary System

An isothermal section of the Ni-Pd-Si system has been established at  $800^\circ\text{C}$  by [1976Wop]. Pure component elements, (99.9 mass %), sealed in evacuated quartz capsules, were melted in a high-frequency induction furnace. Alloys with  $>40$  at.% Si were, however, arc melted. The alloys were prepared between 20 and 65 at.% Si. The alloys sealed in evacuated quartz capsules were annealed for 2 d at  $800^\circ\text{C}$  and water quenched. The annealed alloys were crushed to prepare powder for x-ray diffraction (XRD) work. The powder of the alloys was again annealed at  $800^\circ\text{C}$  for 1 d before taking XRD patterns. The phase analysis of the alloys was done using an XRD method only.

The  $800^\circ\text{C}$  isothermal section of the Ni-Pd-Si system, in a slightly modified form, is shown in Fig. 4. The alloys along the NiSi-PdSi line showed complete solid solubility of the NiSi and PdSi phases ( $\xi$ ) in each other, characteristic of an isomorphous pseudobinary system. Lattice parameter data are shown in Fig. 5.

The  $\text{Pd}_2\text{Si}$  ( $\rho$ ) phase was found to extend into the ternary up to  $\sim 50$  at.% Ni along the  $A_2B$  stoichiometric line. Lattice parameter data are shown in Fig. 6. Along the  $\text{Pd}_3\text{Si}$  ( $\pi$ ) and  $\text{Ni}_{31}\text{Si}_{12}$  ( $\gamma'$ ) line two ternary intermediate phases,  $\text{NiPd}_2\text{Si}$  ( $\Delta$ ) and  $\text{Ni}_{18}\text{Pd}_7\text{Si}_9$  ( $\Gamma$ ), were found to exist as small regions. The  $\text{Pd}_3\text{Si}$  and  $\text{Ni}_{31}\text{Si}_{12}$  phases were found to extend up to  $\sim 9$  at.% Ni and  $\sim 7$  at.% Pd, respectively. The  $\text{Ni}_3\text{Si}_2$  ( $\epsilon$ ) phase was also found to extend into the ternary up to  $\sim 7$

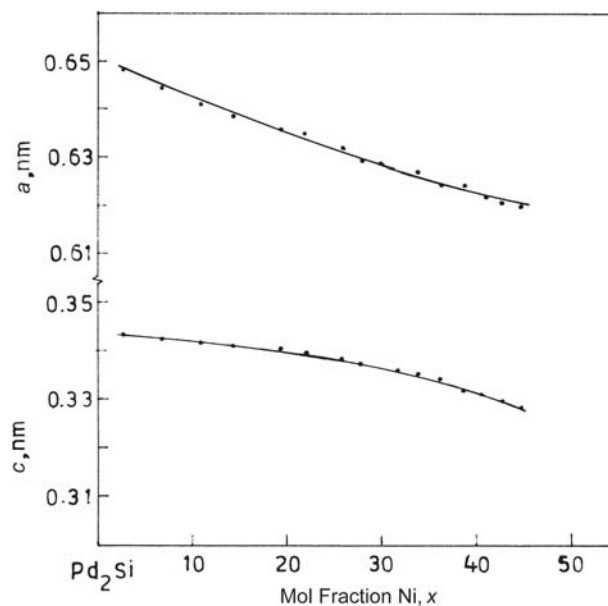


Fig. 6 Lattice parameter of  $\text{Pd}_{66.7-x}\text{Ni}_x\text{Si}_{33.3}$  alloys (annealed at  $900^\circ\text{C}$ ) as a function of Ni content  $x$

at.% Pd. All the other phases  $\text{Ni}_3\text{Si}$  ( $\beta_1$ ),  $\text{Ni}_2\text{Si}$  ( $\delta$ ), and  $\text{NiSi}_2$  ( $\zeta$ ) were found to have only very limited extensions ( $<3$  at.% Pd) into the ternary. The  $\Gamma$  phase was found in equilibrium with the  $\gamma$ ,  $\beta$ ,  $\gamma'$ ,  $\rho$ , and  $\Delta$  phases. The  $\Delta$  phase was found in equilibrium with the  $\gamma$ ,  $\Gamma$ ,  $\rho$ , and  $\pi$  phases.

[1976Wop] have shown in their isothermal section that the binary phases have a solubility range of 2 to 3 at.%. For example, the NiSi and the PdSi phases are single composition (MSi) phases, but are shown to be within  $\sim 2$  at.% solubility range, and accordingly the  $\xi$  phase region in the ternary has been shown to be  $\sim 2$  at.% wide. Because all the  $\xi$  phase alloys were melted along the stoichiometric line between NiSi and PdSi and only XRD was used for phase identification, the  $\xi$  phase boundary given by [1976Wop] (dash-dot line in Fig. 4) is rather doubtful. Hence, in Fig. 4 the  $\xi$  phase is shown only as a single line joining the NiSi and PdSi phases. Similarly, the other binary phases that are single composition phases are shown accordingly in Fig. 4, and the location of the binary phase region adjusted according to the accepted binary data. Further work has to be done to determine the phase boundaries and the proper locations of the three-phase and two-phase regions. Because  $\text{Pd}_4\text{Si}$  and  $\text{Pd}_5\text{Si}$  phases do not exist in the accepted Pd-Si system, these phases are not shown in Fig. 4.

Lattice parameters of  $\rho$  and  $\xi$  phases have been determined as a function of Ni content and are given in Fig. 5 and 6.

The amorphous state of an  $\text{Ni}_{15}\text{Pd}_{65}\text{Si}_{20}$  alloy was produced by the piston and anvil technique [1966Tsu]. On heating the amorphous alloy at  $>20^\circ\text{C}/\text{min}$ , sudden heat evolution of  $\sim 1000$  cal/g · mole was noticed at  $420^\circ\text{C}$ . Below this temperature the alloy was found to transform by a process of nucleation and growth.

## Section II: Phase Diagram Evaluations

### References

**1966Tsu:** C.C. Tsuci and P. Duwez, Metastable Amorphous Ferromagnetic Phases in Pd-Base Alloys, *J. Appl. Phys.*, 1966, **37**, p 435 (Amorphous state)

**1976Wop:** W. Wopersnow and K. Schubert, Nickel-Palladium-Silicon Alloys, *Z. Metallkd.*, 1976, **67**, p 807-810, in German (Phase equilibria; #<sup>1</sup>)

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# indicates presence of a phase diagram.

Ni-Pd-Si evaluation contributed by **K.P. Gupta**, the Indian Institute of Metals, Metal House, Plot 13/4, Block AQ, sector V, Calcutta, India. Literature searched through 1996. Dr. Gupta is the Alloy Phase Diagram Program Co-Category Editor for ternary nickel alloys.